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PAST2: Rev 2; 7/09 EVALUATION KIT AVAILABLE Dual-Phase, Quick-PWM Controllers for IMVP-6+/IMVP-6.5 CPU Core Power Supplies

General Description

The MAX17021/MAX17082/MAX17482 are 2/1-phaseinterleaved Quick-PWM[™] step-down VID power-supply controllers for notebook CPUs. True out-of-phase operation reduces input ripple current requirements and output- voltage ripple, while easing component selection and layout difficulties. The Quick-PWM control provides instantaneous response to fast load-current steps. Active voltage positioning reduces power dissipation and bulk output capacitance requirements and allows ideal positioning compensation for tantalum, polymer, or ceramic bulk output capacitors.

A slew-rate controller allows controlled transitions between VID codes, controlled soft-start and shutdown, and controlled exit from suspend. A thermistor-based temperature sensor provides a programmable thermal-fault output (VRHOT). A current monitor output (IMON) provides an analog current output proportional to the power consumed by the CPU (MAX17082/MAX17482 only). Output undervoltage, overvoltage (MAX17021/MAX17082 only), and thermal protection shut the controller down when any of these faults are detected. A voltage-regulator power-OK (PWRGD) output indicates the output is in regulation. Additionally, the MAX17021/MAX17082/MAX17482 feature true differential current sense and a phase-good (PHASEGD) output that indicates a phase imbalance fault condition.

The MAX17021 supports the IMVP-6+ specification while the MAX17082/MAX17482 support the IMVP-6.5 requirements. The MAX17021/MAX17082/MAX17482 are available in a 5mm x 5mm, 40-pin TQFN package.

Applications

IMVP-6+/IMVP-6.5 Core Supply Multiphase CPU Core Supply Voltage-Positioned, Step-Down Converters Notebook/Desktop Computers Blade Servers

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX17021GTL+	-40°C to +105°C	40 TQFN-EP*
MAX17082GTL+	-40°C to +105°C	40 TQFN-EP*
MAX17482GTL+	-40°C to +105°C	40 TQFN-EP*

+Denotes a lead-free(Pb)/RoHS-compliant package. *EP = Exposed pad.

Quick-PWM is a trademark of Maxim Integrated Products, Inc.

__Features

- Single-/Dual-Phase, Quick-PWM Controllers
- MAX17021 IMVP-6+ (Montevina)
- MAX17082/MAX17482 IMVP-6.5 (Calpella)
- ♦ ±0.5% V_{OUT} Accuracy Over Line, Load, and Temperature
- ♦ 7-Bit 0 to 1.50V VID Control
- Dynamic Phase Selection Optimizes Active/Sleep Efficiency
- Transient Phase Overlap Reduces Output Capacitance
- Integrated Boost Switches
- Active Voltage Positioning with Adjustable Gain
- Programmable 200kHz to 800kHz Switching Frequency
- Accurate Current Balance and Current Limit
- Adjustable Slew-Rate Control
- Power-Good, Clock Enable, and Thermal-Fault Outputs
- Phase Current Imbalance Fault Output
- Drives Large Synchronous Rectifier MOSFETs
- ♦ 4V to 26V Battery Input-Voltage Range
- Undervoltage and Thermal-Fault Protection
- Overvoltage Protection (MAX17021/MAX17082)
- Soft-Startup and Soft-Shutdown

Pin Configuration



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For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

ABSOLUTE MAXIMUM RATINGS

V _{CC} , V _{DD} , V3P3 to GND	0.3V to +6V
	0.3V to +6V
PGDIN, DPRSLPVR, PSI to GND	0.3V to +6V
DPRSTP (MAX17021) to GND	0.3V to +6V
SLOW (MAX17082/MAX17482) to GND	0.3V to +6V
CSP1, CSP2, CSN1, CSN2 to GND	0.3V to +6V
THRM, ILIM, PHASEGD to GND	0.3V to +6V
PWRGD, VRHOT to GND	0.3V to +6V
CLKEN to GND	0.3V to V3P3 + 0.3V
FB, FBAC to GND	0.3V to V _{CC} + 0.3V
TIME, CCI to GND	0.3V to V _{CC} + 0.3V
IMON to GND (MAX17021/MAX17082)	0.3V to V _{CC} + 0.3V
GNDS to GND	0.3V to +0.3V
SHDN to GND (Note 1)	0.3V to +16V
TON to GND	0.3V to +30V

DL1, DL2 to GND	0.3V to V _{DD} + 0.3V
BST1, BST2 to GND	0.3V to +36V
BST1, BST2 to VDD	0.3V to +30V
LX1 to BST1	6V to +0.3V
LX2 to BST2	6V to +0.3V
DH1 to LX1	(-0.3V to V _{BST1}) + 0.3V
DH2 to LX2	(-0.3V to V _{BST2}) + 0.3V
Continuous Power Dissipation	· /
40-Pin 5mm x 5mm TQFN Up to +7	70°C1778mW
(derate above +70°C)	
Operating Temperature Range	40°C to +105°C
Junction Temperature	+150°C
Storage Temperature Range	65°C to +165°C
Lead Temperature (soldering, 10s)	+300°C

Note 1: SHDN might be forced to 12V for the purpose of debugging prototype boards using the no-fault test mode, which disables fault protection and overlapping operation.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 1, V_{IN} = 10V, V_{CC} = V_{DD} = V_{SHDN} = V_{PGDIN} = V_{PSI} = V_{ILIM} = 5V, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN1} = 1.0000V, FB = FBAC, R_{FBAC} = $3.57k\Omega$ from FBAC to CSN1, D6–D0 = [0101000]; MAX17082/MAX17482: V_{SLOW} = 5V; MAX17021: DPRSTP = GND; **T_A** = 0°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.)

PARAMETER	SYMBOL	c	CONDITIONS	MIN	ТҮР	MAX	UNITS
PWM CONTROLLER							
Input Voltago Pango		V _{CC} , V _{DD}		4.5		5.5	V
input-voltage nange		V3P3		3.0		3.6	v
	Vout	Measured at FB with respect to GNDS; includes load- regulation error (Note 2)	DAC codes from 0.8125V to 1.5000V	-0.5		+0.5	%
DC Output-Voltage Accuracy			DAC codes from 0.3750V to 0.8000V	-7		+7	– mV
			DAC codes from 0 to 0.3625V	-20		+20	
Poot Voltago		MAX17021 IMVP-6+		1.194	1.200	1.206	V
Bool vollage	VB001	MAX17082/MAX17482 IMVP-6.5		1.094	1.100	1.106	
Line Regulation Error		$V_{CC} = 4.5V$ to 5.5V,	V _{IN} = 4.5V to 26V		0.1		%
FB Input Bias Current		$T_A = +25^{\circ}C$		-0.1		+0.1	μA
GNDS Input Range				-200		+200	mV
GNDS Gain	Agnds	$\Delta V_{OUT}/\Delta V_{GNDS}$	$\Delta V_{OUT}/\Delta V_{GNDS}$		1.00	1.03	V/V
GNDS Input Bias Current	IGNDS	$T_A = +25^{\circ}C$		-0.5		+0.5	μA
TIME Regulation Voltage	VTIME	$R_{TIME} = 71.5 k\Omega$		1.985	2.000	2.015	V

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{IN} = 10V$, $V_{CC} = V_{DD} = V_{\overline{SHDN}} = V_{PGDIN} = V_{\overline{PSI}} = V_{ILIM} = 5V$, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, $V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN1} = 1.0000V$, FB = FBAC, $R_{FBAC} = 3.57k\Omega$ from FBAC to CSN1, D6-D0 = [0101000]; MAX17082/MAX17482: $V_{\overline{SLOW}} = 5V$; MAX17021: DPRSTP = GND; $T_A = 0^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.)

PARAMETER	SYMBOL		CONDITIONS	MIN	ТҮР	MAX	UNITS
		R _{TIME} = 71	.5k Ω (12.5mV/ μ s nominal)	-10		+10	
		R _{TIME} = 35 (5mV/µs no	.7k Ω (25mV/µs nominal) to 178k Ω minal)	-15		+15	
		Soft-start ar R _{TIME} = 35 (0.625mV/µ	Soft-start and soft-shutdown: $R_{TIME} = 35.7 k\Omega (3.125 mV/\mu s nominal) to 178 k\Omega$ (0.625 mV/µs nominal)			+25	
TIME Slew-Rate Accuracy		Slow: IMVP-6.5 (M 1/2 of nomin (6.25mV/µs IMVP-6+ (M 1/4 of nomin (3.125mV/µ	MAX17082/MAX17482): $V_{\overline{SLOW}} = 0V$, nal slew rate, $R_{TIME} = 71.5k\Omega$ nominal); AX17021): $V_{\overline{DPRSTP}} = V_{DPRSLPVR} = 5V$, nal slew rate, $R_{TIME} = 71.5k\Omega$ s nominal)	-15		+15	%
		Slow: IMVP-6.5 (N 1/2 of nomi (12.5mV/µs nominal); IMVP-6+ (N 1/4 of nomi (6.25mV/µs nominal)	MAX17082/MAX17482): $V_{SLOW} = 0V$, nal slew rate, $R_{TIME} = 35.7 k\Omega$ nominal) to $178 k\Omega$ (2.5mV/µs MAX17021): $V_{DPRSTP} = V_{DPRSLPVR} = 5V$ nal slew rate, $R_{TIME} = 35.7 k\Omega$ nominal) to $178 k\Omega$ (1.25mV/µs	-15		+15	
		Measured at DH_ (Note 2)	$R_{TON} = 96.75 k\Omega (600 kHz per phase),$ 167ns nominal	-15		+15	
On-Time	ton		R _{TON} = 200kΩ (300kHz per phase), 333ns nominal	-10		+10	%
		($R_{TON} = 303.25 k\Omega (200 kHz per phase),$ 500ns nominal	-15		+15	
Minimum Off-Time	toff(MIN)	Measured a	at DH_ (Note 3)		300	350	ns
TON Shutdown Input Current	IRTON,SDN	$\overline{SHDN} = GN$ $T_A = +25^{\circ}C$	ND, $V_{IN} = 26V$, $V_{CC} = V_{DD} = 0V$ or 5V,		0.01	0.1	μA
BIAS CURRENTS							
Quiescent Supply Current (V _{CC})	ICC	Measured a above the r	at V_{CC} , $V_{DPRSLPVR} = 5V$, FB forced egulation point		2.5	5	mA
Quiescent Supply Current (V _{DD})	IDD	Measured a above the r	at V _{DD} , V _{DPRSLPVR} = 0V, FB forced egulation point, T _A = $+25^{\circ}$ C		0.02	1	μA

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{IN} = 10V$, $V_{CC} = V_{DD} = V_{\overline{SHDN}} = V_{PGDIN} = V_{\overline{PSI}} = V_{ILIM} = 5V$, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, $V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN1} = 1.0000V$, FB = FBAC, $R_{FBAC} = 3.57k\Omega$ from FBAC to CSN1, D6-D0 = [0101000]; MAX17082/MAX17482: $V_{\overline{SLOW}} = 5V$; MAX17021: DPRSTP = GND; $T_A = 0^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.)

PARAMETER	SYMBOL	CONDITIONS	3	MIN	ТҮР	МАХ	UNITS
Quiescent Supply Current (V3P3)	I _{3P3}	Measured at V3P3, FB forced w power-good window	ithin the CLKEN		2	4	μA
Shutdown Supply Current (V _{CC})	ICC,SDN	Measured at V_{CC} , $\overline{SHDN} = GNE$	D, T _A = +25°C		0.01	1	μA
Shutdown Supply Current (V _{DD})	I _{DD,SDN}	Measured at V_{DD} , $\overline{SHDN} = GNE$	D, T _A = +25°C		0.01	1	μA
Shutdown Supply Current (V3P3)	I3P3,SDN	Measured at V3P3, SHDN = GN	ID, T _A = +25°C		0.01	1	μA
FAULT PROTECTION							
Output Overvoltage-		Skip mode after output reaches voltage or PWM mode; measure respect to the voltage target se see Table 4.	Skip mode after output reaches the regulation voltage or PWM mode; measured at FB with respect to the voltage target set by the VID code; see Table 4.		300	350	mV
Protection Threshold (MAX17021/MAX17082 Only)	VOVP	Soft-start, soft-shutdown, skip mode, and output have not	IMVP-6.5 (MAX17082)	1.45	1.50	1.55	V
		reached the regulation voltage; measured at FB	IMVP-6+ (MAX17021)	1.75	1.80	1.85	
		Minimum OVP threshold; meas	ured at FB		0.8		
Output Overvoltage- Propagation Delay (MAX17021/MAX17082 Only)	tovp	FB forced 25mV above trip threshold			10		μs
Output Undervoltage- Protection Threshold	VUVP	Measured at FB with respect to set by the VID code; see Table	the voltage target 4	-450	-400	-350	mV
Output Undervoltage- Propagation Delay	tuvp	FB forced 25mV below trip three	shold		10		μs
CLKEN Startup Delay and Boot Time Period	tвоот	Measured from the time when F boot target voltage (Note 2)	B reaches the	20	60	100	μs
PWRGD Startup Delay		Measured at startup from the til goes low	me when CLKEN	3	6.5	10	ms
CLKEN and PWRGD		Measured at FB with respect to the voltage target set by	Lower threshold, falling edge (undervoltage)	-350	-300	-250	
Threshold		the VID code; see Table 4, 20mV hysteresis (typ)	Upper threshold, rising edge (overvoltage)	+150	+200	+250	
CLKEN and PWRGD Delay		FB forced 25mV outside the PV thresholds	/RGD trip		10		μs
PHASEGD Delay		V(CCI,FB) forced 25mV outside t	rip thresholds		10		μs

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{IN} = 10V$, $V_{CC} = V_{DD} = V_{\overline{SHDN}} = V_{PGDIN} = V_{\overline{PSI}} = V_{ILIM} = 5V$, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, $V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN1} = 1.0000V$, FB = FBAC, $R_{FBAC} = 3.57k\Omega$ from FBAC to CSN1, D6-D0 = [0101000]; MAX17082/MAX17482: $V_{\overline{SLOW}} = 5V$; MAX17021: DPRSTP = GND; $T_A = 0^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.)

PARAMETER	SYMBOL	C	ONDITIONS	MIN	ТҮР	MAX	UNITS
CLKEN, PWRGD, and PHASEGD Transition Blanking Time (VID Transitions)	^t BLANK	Measured from the ti target voltage (Note	ime when FB reaches the 2)		20		μs
PHASEGD Transition Blanking Time (Phase 2 Enable Transitions)		Number of DH2 puls blanked after phase	es for which PHASEGD is 2 is enabled		32		Pulses
CLKEN Output Low Voltage		Low state, ISINK = 3	mA			0.4	V
CLKEN Output High Voltage		High state, ISOURCE	= 3mA	V3P3 - 0.4			V
PWRGD, PHASEGD Output Low Voltage		Low state, I _{SINK} = 3mA				0.4	V
PWRGD, PHASEGD Leakage Current		High-impedance sta to 5V, T _A = +25°C	te, PWRGD, PHASEGD forced			1	μΑ
CSN1 Pulldown Resistance in Shutdown		SHDN = 0, measured completed (DL_ = lo	d after soft-shutdown w)		10		Ω
V _{CC} Undervoltage Lockout (UVLO) Threshold	VUVLO(VCC)	Rising edge, 65mV t controller disabled b	Rising edge, 65mV typical hysteresis, controller disabled below this level			4.48	V
THERMAL PROTECTION				•			
VRHOT Trip Threshold		Measured at THRM a falling edge, typical	as a percentage of V _{CC} , hysteresis = 75mV	29	30	31	%
VRHOT Delay	t <u>vrhot</u>	THRM forced 25mV threshold, falling edg	below the VRHOT trip ge		10		μs
VRHOT Output On-Resistance	R _{ON} (VRHOT)	Low state			2	10	Ω
VRHOT Leakage Current		High-impedance sta T _A = +25°C	te, $\overline{\text{VRHOT}}$ forced to 5V,			1	μΑ
THRM Input Leakage	ITHRM	$V_{\text{THRM}} = 0$ to 5V, T_{A}	= +25°C	-0.1		+0.1	μΑ
Thermal-Shutdown Threshold	T _{SHDN}	Typical hysteresis =	= 15°C		160		°C
VALLEY CURRENT LIMIT, D	ROOP, AND	CURRENT BALANCE	-				_
Current Limit Threehold			V _{TIME} - V _{ILIM} = 100mV	7	10	13	
Voltage (Positive)	VLIMIT	VCSP VCSN_	VTIME - VILIM = 500mV	45	50	55	mV
,			$ILIM = V_{CC}$	20	22.5	25	
Current-Limit Threshold Voltage (Negative) Accuracy	VLIMIT(NEG)	VCSP VCSN_, nomi	V _{CSP} - V _{CSN} , nominally -125% of V _{LIMIT}			+4	mV
Current-Limit Threshold Voltage (Zero Crossing)	VZERO	V _{GND} - V _{LX_} , DPRSLF	PVR = 5V		1		mV



ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{IN} = 10V$, $V_{CC} = V_{DD} = V_{\overline{SHDN}} = V_{PGDIN} = V_{\overline{PSI}} = V_{ILIM} = 5V$, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, $V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN1} = 1.0000V$, FB = FBAC, $R_{FBAC} = 3.57k\Omega$ from FBAC to CSN1, D6-D0 = [0101000]; MAX17082/MAX17482: $V_{\overline{SLOW}} = 5V$; MAX17021: DPRSTP = GND; $T_A = 0^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.)

PARAMETER	SYMBOL	COND	ITIONS		MIN	ТҮР	МАХ	UNITS
CSP_, CSN_ Common- Mode Input Range					0		2	V
Phase 2 Disable Threshold		Measured at CSP2			3	V _{CC} - 1	V _{CC} - 0.4	V
CSP_, CSN_ Input Current	ICSP_, ICSN_	$T_A = +25^{\circ}C$			-0.2		+0.2	μA
ILIM Input Current	IILIM	$T_A = +25^{\circ}C$			-0.1		+0.1	μA
Droop Amplifier Offset		$(1/N) \times \Sigma (V_{CSP} - V_{CSN})$ IFBAC = 0; Σ indicates summation c	at -	T _A = +25°C	-0.5		+0.5	mV/ phase
		all phases from 1 to N, N	1 = 2	$I_A = 0^{\circ}C \text{ to } +85^{\circ}C$	-0.75		+0.75	
Droop Amplifier Transconductance	G _{m(FBAC)}	$ \Delta I_{FBAC} \Delta [\Sigma (V_{CSP} - V_{CSN})]; $ $ \Sigma \text{ indicates summation over all phases from 1 to} $ $ N, N = 2, V_{FBAC} = V_{CSN-} = 0.45V \text{ to } 2V $		590	600	608	μS	
Current-Balance Amplifier Offset		(VCSP1 - VCSN1) - (VCSP2 -	VCSN2)) at $I_{CCI} = 0$	-1.0		+1.0	mV
Current-Balance Amplifier Transconductance	G _{m(CCI)}	I _{CCI} /[(V _{CSP1} - V _{CSN1}) - (V _{CSP2} - V _{CSN2})]				200		μS
CURRENT MONITOR (MAX1	7082/MAX174	182 Only)						
Current-Monitor Output Current at Full Load Condition	IIMON	$V_{CSP1} - V_{CSN1} = V_{CSP2} - V_{CSN_} = 0.45V \text{ to } 2.0V$	$V_{CSP1} - V_{CSN1} = V_{CSP2} - V_{CSN2} = 20mV,$ $V_{CSN_} = 0.45V \text{ to } 2.0V$		93.12	96	98.88	μA
Current-Monitor Transconductance	G _m (IMON)	$ \frac{\Delta I_{IMON}}{\Delta} \frac{\Sigma}{\Sigma} (V_{CSP} - V_{CSN}) $ $ \frac{\Sigma}{\Sigma} \text{ indicates summation c} $ $ N, N = 2, CSN_{-} = 0.45V \text{ t} $	N_)]; over all to 2V	phases from 1 to	2.2	2.4	2.6	mS
IMON Clamp Voltage	VIMON,max	I _{SINK} = 10mA			1.05	1.10	1.15	V
IMON Pulldown Resistance in Shutdown		SHDN = 0, measured after completed (DL_ = low)	er soft-s	shutdown		10		Ω
GATE DRIVERS		· · · · · · · · · · · · · · · · · · ·						
DH_Gate Driver		BST - LX forced to 5V	High s	state (pullup)		0.9	2.5	0
On-Resistance			Low s	tate (pulldown)		0.7	2.0	
DL_Gate Driver	RON(DL)		High s	state (pullup)		0.7	2.0	Ω
On-Resistance	0.1(0.2_)		Low s	tate (pulldown)		0.25	0.7	
DH_ Gate Driver Source Current	IDH_(SOURCE)	DH_ forced to 2.5V, BST_	LX_ f	forced to 5V		2.2		A
DH_ Gate Driver Sink Current	IDH_(SINK)	DH_ forced to 2.5V, BST_	LX_ f	forced to 5V		2.7		A
DL_ Gate Driver Source Current	IDL_(SOURCE)	DL_ forced to 2.5V				2.7		A

M/IXI/M

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{IN} = 10V$, $V_{CC} = V_{DD} = V_{\overline{SHDN}} = V_{PGDIN} = V_{\overline{PSI}} = V_{ILIM} = 5V$, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, $V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN1} = 1.0000V$, FB = FBAC, $R_{FBAC} = 3.57k\Omega$ from FBAC to CSN1, D6-D0 = [0101000]; MAX17082/MAX17482: $V_{\overline{SLOW}} = 5V$; MAX17021: $\overline{DPRSTP} = GND$; $T_{A} = 0^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_{A} = +25^{\circ}C$.)

	1					
PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
DL_ Gate Driver Sink Current	I _{DL_(SINK)}	DL_ forced to 2.5V		8		A
Internal BST_Switch On-Resistance	R _{ON(BST_)}			10	20	Ω
LOGIC AND I/O						
Logic Input High Voltage	VIH	SHDN, PGDIN MAX17021: DPRSLPVR	2.3			V
Logic Input Low Voltage	VIL	SHDN, PGDIN MAX17021: DPRSLPVR			1.0	V
SHDN No-Fault Level		To enable no-fault mode	11		13	V
Low-Voltage Logic Input High Voltage	VIHLV	PSI, D0–D6; MAX17082/MAX17482: DPRSLPVR, SLOW, MAX17021: DPRSTP	0.67			V
Low-Voltage Logic Input Low Voltage	VILLV	PSI, D0–D6; MAX17082/MAX17482: DPRSLPVR, SLOW, MAX17021: DPRSTP			0.33	V
Logic Input Current		$T_A = +25^{\circ}C$, \overline{SHDN} , DPRSLPVR, PGDIN, \overline{PSI} , DPRSTP, SLOW, D0–D6 = 0 or 5V	-1		+1	μA

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 1, V_{IN} = 10V, V_{CC} = V_{DD} = V_{SHDN} = V_{PGDIN} = V_{PSI} = V_{ILIM} = 5V, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN2} = 1.0000V, FB = FBAC, R_{FBAC} = $3.57k\Omega$ from FBAC to CSN1, D6–D0 = [0101000]; MAX17082/MAX17482: V_{SLOW} = 5V; MAX17021: DPRSTP = GND; **T_A** = -40°C to +105°C, unless otherwise noted.) (Note 4)

PARAMETER	SYMBOL	CON	DITIONS	MIN	ТҮР	MAX	UNITS	
PWM CONTROLLER				·			•	
		V _{CC} , V _{DD}		4.5		5.5	V	
Input-voltage hange	SYMBOL CONDITIONS VCC, VDD V3P3 V3P3 VOUT Measured at FB with respect to GNDS; includes load-regulation error (Note 2) DAC codes from 0.8125V to 1.5000V DAC codes from 0.3750V to 0.8000V DAC codes from 0.3750V to 0.8000V VBOOT MAX17021: IMVP-6+ WBOOT MAX17082/MAX17482: IMVP-6.5		3.0		3.6	V		
	Vout	Measured at FB with respect to GNDS; includes load-	DAC codes from 0.8125V to 1.5000V	-0.75		+0.75	%	
DC Output-Voltage Accuracy			DAC codes from 0.3750V to 0.8000V	-10		+10		
		regulation error (Note 2)	DAC codes from 0 to 0.3625V	-25		+25		
	Vacar	MAX17021: IMVP-6+		1.19		1.21		
DC Output-Voltage Accuracy Boot Voltage	VBOOT	MAX17082/MAX17482: IMVP-6.5		1.09		1.11	V	

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{IN} = 10V$, $V_{CC} = V_{DD} = V_{\overline{SHDN}} = V_{PGDIN} = V_{\overline{PSI}} = V_{ILIM} = 5V$, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, $V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN2} = 1.0000V$, FB = FBAC, $R_{FBAC} = 3.57k\Omega$ from FBAC to CSN1, D6-D0 = [0101000]; MAX17082/MAX17482: $V_{\overline{SLOW}} = 5V$; MAX17021: DPRSTP = GND; $T_{A} = -40^{\circ}C$ to $+105^{\circ}C$, unless otherwise noted.) (Note 4)

PARAMETER	SYMBOL		CONDITIONS	MIN	ТҮР	МАХ	UNITS	
GNDS Input Range				-200		+200	mV	
GNDS Gain	Agnds	ΔVOUT/ΔV	GNDS	0.97		1.03	V/V	
TIME Regulation Voltage	VTIME	R _{TIME} = 7	1.5k Ω	1.985		2.015	V	
		$R_{TIME} = 71.5 k\Omega (12.5 mV/\mu s nominal)$		-10		+10		
		RτιME = 3 (5mV/μs n	5.7k Ω (25mV/µs nominal) to 178k Ω ominal)	-15		+15		
		Soft-start a R _{TIME} = 3 (0.625mV/	nd soft-shutdown: 5.7kΩ (3.125mV/μs nominal) to 178kΩ us nominal)	-25		+25		
Slow:IMVP-6.5 (MAX17082/MAX17482): $V_{SLOW} = 0V$ 1/2 of nominal slew rate, $R_{TIME} = 71.5k\Omega$ (6.25mV/µs nominal);IMVP-6+ (MAX17021): $V_{DPRSTP} = V_{DPRSLPVR} = 5$ 1/4 of nominal slew rate, $R_{TIME} = 71.5k\Omega$ (3.125mV/µs nominal)Slow:IMVP-6.5 (MAX17082/MAX17482): $V_{SLOW} = 0V$,1/2 of nominal slew rate, $R_{TIME} = 35.7k\Omega$ (12.5mV/µs nominal) to 178kΩ (2.5mV/µs nominal)Slow:IMVP-6+ (MAX17021): $V_{DPRSTP} = V_{DPRSLPVR} = 5$ 1/4 of nominal slew rate, $R_{TIME} = 35.7k\Omega$ (6.25mV/µs nominal) to 178kΩ (1.25mV/µs nominal)IMVP-6+ (MAX17021): $V_{DPRSTP} = V_{DPRSLPVR} = 5$ 1/4 of nominal slew rate, $R_{TIME} = 35.7k\Omega$ (6.25mV/µs nominal) to 178kΩ (1.25mV/µs nominal)RTON = 96.75kΩ (600kHz per phase)167ns nominalRTON = 200kΩ (300kHz per phase)		Slow: IMVP-6.5 (MAX17082/MAX17482): $V_{SLOW} = 0V$, 1/2 of nominal slew rate, $R_{TIME} = 71.5k\Omega$ (6.25mV/µs nominal); IMVP-6+ (MAX17021): $V_{DPRSTP} = V_{DPRSLPVR} = 5V$, 1/4 of nominal slew rate, $R_{TIME} = 71.5k\Omega$ (3.125mV/µs nominal)				+15	%	
	MAX17082/MAX17482): $V_{SLOW} = 0V$, inal slew rate, $R_{TIME} = 35.7k\Omega$ s nominal) to 178k Ω (2.5mV/µs nominal); MAX17021): $V_{DPRSTP} = V_{DPRSLPVR} = 5V$, inal slew rate, $R_{TIME} = 35.7k\Omega$ s nominal) to 178k Ω (1.25mV/µs nominal)	-17		+17				
			$R_{TON} = 96.75 k\Omega$ (600kHz per phase), 167ns nominal	-15		+15		
On-Time	ton	Measured at DH_ (Note 3)	R _{TON} = 200kΩ (300kHz per phase), 333ns nominal	-15		+15	%	
			R _{TON} = 303.25kΩ (200kHz per phase), 500ns nominal	-15		+15		
Minimum Off-Time	toff(MIN)	Measured	at DH_ (Note 3)			350	ns	
BIAS CURRENTS				-				
Quiescent Supply Current (V _{CC})	ICC	Measured above the	at V_{CC} , $V_{DPRSLPVR} = 5V$, FB forced regulation point			5	mA	
Quiescent Supply Current (V3P3)	I _{3P3}	Measured power-goo	at V3P3, FB forced within the CLKEN d window			4	μA	

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{IN} = 10V$, $V_{CC} = V_{DD} = V_{\overline{SHDN}} = V_{PGDIN} = V_{\overline{PSI}} = V_{ILIM} = 5V$, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, $V_{CSP1} = V_{CSN1} = V_{CSN2} = V_{CSN2} = 1.0000V$, FB = FBAC, $R_{FBAC} = 3.57k\Omega$ from FBAC to CSN1, D6–D0 = [0101000]; MAX17082/MAX17482: $V_{\overline{SLOW}} = 5V$; MAX17021: DPRSTP = GND; **TA = -40°C to +105°C**, unless otherwise noted.) (Note 4)

PARAMETER	SYMBOL	CONDITIONS		MIN	ТҮР	MAX	UNITS
FAULT PROTECTION							•
Output Overvoltage- Protection Threshold	Maria	Skip mode after output reaches th voltage or PWM mode, measured respect to the voltage target set b (see Table 4)	Skip mode after output reaches the regulation voltage or PWM mode, measured at FB with respect to the voltage target set by the VID code (see Table 4)			350	mV
(MAX17021/MAX7082 Only)	VOVP	Soft-start, soft-shutdown, skip mode, and output have not	IMVP-6.5 (MAX17082)	1.45		1.55	
		reached the regulation voltage, measured at FB	IMVP-6+ (MAX17021)	1.75		1.85	v
Output Undervoltage- Protection Threshold	VUVP	Measured at FB with respect to th set by the VID code (see Table 4)	e voltage target	-450		-350	mV
CLKEN Startup Delay and Boot Time Period	^t воот	Measured from the time when FB boot target voltage (Note 3)	reaches the	20		100	μs
PWRGD Startup Delay		Measured at startup from the time goes low	Measured at startup from the time when CLKEN goes low			10	ms
CLKEN and PWBGD		Measured at FB with respect to the voltage target set by the VID	Lower threshold, falling edge (undervoltage)	-350		-250	
Threshold		code (see Table 4), 20mV hysteresis (typ)	Upper threshold, rising edge (overvoltage)	+150		+250	mv
CLKEN Output Low Voltage		Low state, I _{SINK} = 3mA				0.4	V
CLKEN Output High Voltage		High state, I _{SOURCE} = 3mA		V3P3 - 0.4			V
PWRGD, PHASEGD Output Low Voltage		Low state, I _{SINK} = 3mA				0.4	V
V _{CC} Undervoltage-Lockout Threshold (UVLO)	VUVLO(VCC)	Rising edge, 65mV typical hyster disabled below this level	esis, controller	4.0		4.5	V
THERMAL PROTECTION							
VRHOT Trip Threshold		Measured at THRM as a percenta falling edge, typical hysteresis =	ige of V _{CC} , 75mV	28		32	%
VRHOT Output On-Resistance	R _{ON} (VRHOT)	Low state				10	Ω

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 1, $V_{IN} = 10V$, $V_{CC} = V_{DD} = V_{\overline{SHDN}} = V_{PGDIN} = V_{\overline{PSI}} = V_{ILIM} = 5V$, V3P3 = 3.3V, DPRSLPVR = GNDS = GND, $V_{CSP1} = V_{CSN1} = V_{CSP2} = V_{CSN2} = 1.0000V$, FB = FBAC, $R_{FBAC} = 3.57k\Omega$ from FBAC to CSN1, D6-D0 = [0101000]; MAX17082/MAX17482: $V_{\overline{SLOW}} = 5V$; MAX17021: DPRSTP = GND; $T_A = -40^{\circ}C$ to $+105^{\circ}C$, unless otherwise noted.) (Note 4)

PARAMETER	SYMBOL	CONDITIONS		MIN	ТҮР	МАХ	UNITS
VALLEY CURRENT LIMIT, DROOP, AND CURRENT BALANCE							
		,	VTIME - VILIM = 100mV	7		13	
Voltage (Positive)	VLIMIT	V _{CSP} - V _{CSN}	VTIME - VILIM = 500mV	40		60	mV
Voltage (1 Ostrive)			$ILIM = V_{CC}$	19		26	
CSP_, CSN_ Common-Mode Input Range				0		2	V
Droop Amplifier Transconductance	Gm(FBAC)	$ \begin{split} &\Delta I_{FBAC} / \Delta [\Sigma (V_{CSP_} - V_{CSN_})], \\ &\Sigma \text{ indicates summation over all phases from 1 to} \\ &N, N = 2, V_{FBAC} = V_{CSN-} = 0.45V \text{ to } 2V \end{split} $		585		610	μS
Current-Balance Amplifier Offset		$(V_{CSP1} - V_{CSN1}) - (V_{CSP2} - V_{CSN2})$ at $I_{CC1} = 0$		-1.25		+1.25	mV
CURRENT MONITOR (MAX1	7082/MAX17	482 Only)					
Current-Monitor Transconductance	G _{m(IMON)}	$ \Delta I_{IMON} \Delta [\Sigma (V_{CSP} - V_{CSN})], $ Σ indicates summation over all phases from 1 to N, N = 2, V_{CSN} = 0.45V to 2V		2.2		2.6	mS
IMON Clamp Voltage	VIMON,max	I _{SINK} = 10mA		1.05		1.15	V
GATE DRIVERS							
DH_Gate Driver		High state (pullup)				2.5	0
On-Resistance	non(DH_)		Low state (pulldown)		2.0		52
DL_Gate Driver			High state (pullup)			2.0	Ω
On-Resistance			Low state (pulldown)			0.7	
LOGIC AND I/O							
Logic Input High Voltage	VIH	SHDN, PGDIN: MAX17021: DPRSLPVF	3	2.3			V
Logic Input Low Voltage	VIL	SHDN, PGDIN: MAX17021: DPRSLPVR				1.0	V
Low-Voltage Logic Input High Voltage	VIHLV	PSI, D0–D6: MAX17082/MAX17482: DPRSLPVR, SLOW MAX17021: DPRSTP		0.67			V
Low-Voltage Logic Input Low Voltage	VILLV	PSI, D0–D6: MAX17082/MAX17482: DPRSLPVR, SLOW MAX17021: DPRSTP				0.33	V

Note 2: When pulse skipping, the output rises by approximately 1.5% when transitioning from continuous conduction to no load.

Note 3: On-time and minimum off-time specifications are measured from 50% to 50% at the DH_ and DL_ pins, with LX_ forced to GND, BST_ forced to 5V, and a 500pF capacitor from DH_ to LX_ to simulate external MOSFET gate capacitance. Actual incircuit times might be different due to MOSFET switching speeds.

Note 4: Specifications to $T_A = -40^{\circ}C$ and $+105^{\circ}C$ are guaranteed by design and are not production tested.



Typical Operating Characteristics

(Circuit of Figure 1. V_{IN} = 12V, V_{CC} = V_{DD} = 5V, SHDN = V_{CC}, D0–D6 set for 1.075V, T_A = +25°C, unless otherwise specified.)



D. CLKEN, 10V/div



Typical Operating Characteristics (continued)

= 100

608 610

 $I_{OUT} = 15A$

A

В

С

D

(Circuit of Figure 1. $V_{IN} = 12V$, $V_{CC} = V_{DD} = 5V$, $\overline{SHDN} = V_{CC}$, D0–D6 set for 1.075V, $T_A = +25^{\circ}C$, unless otherwise specified.)





MAX17021/MAX17082/MAX17482

Typical Operating Characteristics (continued)

(Circuit of Figure 1. V_{IN} = 12V, V_{CC} = V_{DD} = 5V, SHDN = V_{CC}, D0–D6 set for 1.075V, T_A = +25°C, unless otherwise specified.)



Typical Operating Characteristics (continued)

(Circuit of Figure 1. V_{IN} = 12V, V_{CC} = V_{DD} = 5V, \overline{SHDN} = V_{CC} , D0–D6 set for 1.075V, T_A = +25°C, unless otherwise specified.)





Pin Description

PIN	NAME	FUNCTION
1	PGDIN	System Power-Good Logic Input. PGDIN indicates the power status of other system rails and is used for power-supply sequencing. After power-up to the boot voltage, the output voltage remains at V _{BOOT} , CLKEN remains high, and PWRGD remains low as long as the PGDIN stays low. When PGDIN is pulled high, the output transitions to selected VID voltage, and CLKEN is pulled low. If the system pulls PGDIN low during normal operation, the MAX17021/MAX17082/MAX17482 immediately drive CLKEN high, pull PWRGD low, and slew the output to the boot voltage (using two-phase pulse-skipping mode). The controller remains at the boot voltage until PGDIN goes high again, SHDN is toggled, or the V _{CC} input power supply is cycled.
2	THRM	Input of Internal Comparator. Connect the output of a resistor- and thermistor-divider (between V_{CC} and GND) to THRM. Select the components such that the voltage at THRM falls below 1.5V (30% of V_{CC}) at the desired high temperature.
3	IMON (MAX17082/ MAX17482 only)	Current-Monitor Output. The MAX17082/MAX17482 IMON output source a current that is directly proportional to the current-sense voltage as defined by: IIMON = Gm(IMON) × (VCSP VCSN_) where Gm(IMON) = 2.4mS (typ). The IMON current is unidirectional (sources current out of IMON only) for positive current-sense values. For negative current-sense voltages, the IMON current is zero. Connect an external resistor between IMON and VSS_SENSE to create the desired IMON gain based on the following equation: RIMON = 0.999V/(IMAX × RSENSE × Gm(IMON)) where IMAX is defined in the <i>Current Monitor</i> section of the Intel IMVP-6.5 specification and based on discrete increments (20A, 30A, 40A, etc.), RSENSE is the typical effective value of the current-sense element (sense resistor or inductor DCR) that is used to provide the current-sense voltage, and Gm(IMON) is the typical transconductance amplifier gain as defined in the <i>Electrical Characteristics</i> table. The IMON voltage is internally clamped to a maximum of 1.1V (typ). The transconductance amplifier and voltage clamp are internally compensated, so IMON cannot directly drive large capacitance values. To filter the IMON signal, use an RC filter as shown in Figure 2. IMON is pulled to ground when MAX17082/MAX17482 are in shutdown.



Pin Description (continued)

PIN	NAME	FUNCTION
4	ILIM	Valley Current-Limit Adjustment Input. The valley current-limit threshold voltage at CSP_ to CSN_ equals precisely 1/10 of the differential TIME to ILIM voltage over a 0.1V to 0.5V range (10mV to 50mV current-sense range). The negative current-limit threshold is nominally -125% of the corresponding valley current-limit threshold. Connect ILIM directly to V _{CC} to set the default current-limit threshold setting of 22.5mV (typ) nominal.
5	TIME	Slew-Rate Adjustment Pin. TIME regulates to 2.0V and the load current determines the slew rate of the internal error-amplifier target. The sum of the resistance between TIME and GND (R_{TIME}) determines the nominal slew-rate: SLEW RATE = (12.5 mV/µs) × (71.5 kΩ/RTIME) The guaranteed R_{TIME} range is between 35.7kΩ and 178kΩ. This "nominal" slew rate applies to VID transitions and to the transition from boot mode to VID. If the VID DAC inputs are clocked, the slew rate for all other VID transitions is set by the rate at which they are clocked, up to a maximum slew rate equal to the nominal slew rate defined above. The startup and shutdown slew rates are always 1/8 of nominal slew rate in order to minimize surge currents. MAX17021: If both DPRSLPVR and DPRSTP are pulled high, then the slew rate is reduced to 1/4 of nominal. MAX17082/MAX17482: If SLOW is low, then the slew rate is reduced to 1/2 of nominal.
6	Vcc	Controller Analog Bias Supply Voltage. Connect to a 4.5V to 5.5V source. Bypass to GND with 1µF minimum.
7	CCI	Current-Balance Compensation. Connect a 470pF capacitor between CCI and the positive side of the feedback remote sense. CCI is internally forced low in shutdown.
8	FB	Remote Feedback-Sense Input. Normally shorted to FBAC and connected to the VCC_SENSE pin of the CPU socket through the load-line gain resistor (see the FBAC pin description). FB internally connects to the error amplifier and integrator.
9	FBAC	Voltage-Positioning Transconductance Amplifier Output. Connect a resistor R _{FB} between FBAC and the positive side of the feedback remote sense to set the DC steady-state droop based on the voltage-positioning gain requirement: $R_{FB} = R_{DROOP}/(R_{SENSE} \times G_m(FBAC))$ where R _{DROOP} is the desired voltage-positioning slope and G _{m(FBAC}) = 600µS (typ). R _{SENSE} is the value of the current-sense resistors that are used to provide the (CSP_, CSN_) current-sense voltages. If lossless sensing is used, R _{SENSE} = R _L . In this case, consider making R _{FB} a resistor network that includes an NTC thermistor to minimize the temperature dependence of the voltage-positioning slope. FBAC is high impedance in shutdown.
10	GNDS	Remote Ground-Sense Input. Normally connected to the VSS_SENSE pin of the CPU socket. GNDS internally connects to a transconductance amplifier that fine tunes the output voltage—compensating for voltage drops from the regulator ground to the load ground.
11	CSN2	Negative Current-Sense Input for Phase 2. Connect CSN2 to the negative terminal of the inductor current-sensing resistor or directly to the negative terminal of the inductor if the lossless DCR sensing method is used (see Figure 4).
12	CSP2	Positive Current-Sense Input for Phase 2. Connect CSP2 to the positive terminal of the inductor current- sensing resistor or directly to the positive terminal of the filtering capacitor used when the lossless DCR sensing method is used (see Figure 4). Short CSP2 to V_{CC} for dedicated one-phase operation.

Pin Description (continued)

PIN	NAME	FUNCTION		
13	SHDN	Shutdown Control Input. This input cannot withstand the battery voltage. Connect to V_{CC} for normal operation. Connect to ground to put the IC into its 1µA max shutdown state. During startup, the output voltage is ramped up to the boot voltage slowly at a slew rate that is 1/8 the slew rate set by the TIME resistor. During the transition from normal operation to shutdown, the output voltage is ramped down at the same slow slew rate. Forcing SHDN to 11V~13V disables both overvoltage-protection and undervoltage-protection circuits, clears the fault latch, disables transient phase overlap, and disables the BST_ charging switches. Do not connect SHDN to > 13V.		
14	DPRSLPVR	Pulse-Skipping Control Input. This 1.0V logic input signal indicates power usage and sets the operating mode of MAX17021/MAX17082/MAX17482. When DPRSLPVR is forced high, the controller immediately enters the automatic pulse-skipping mode. The controller returns to forced-PWM mode when DPRSLPVR is forced low and the output is in regulation. The PWRGD upper threshold is blanked during any downward output-voltage transition that occurs when the controller is in pulse-skipping mode, and stays blanked until the transition-related PWRGD blanking period is complete and the output reaches regulation. The output overvoltage fault threshold is changed from a tracking [VID + 300mV] threshold to a fixed-default transitional OVP threshold during the period for which the PWRGD upper threshold is blanked. The MAX17082 is in two-phase pulse-skipping mode during startup and while in boot mode, but is in forced-PWM mode during the transition from boot mode to VID mode plus 20µs, and during softshudown, irrespective of the DRPSLPVR logic level. DPRSLPVR PSI MODE AND PHASES 1 0 Very low current (one-phase pulse skipping) 0 0 Intermediate power potential (one-phase PWM) 0 0 Intermediate power potential (one-phase PWM)		
15	PSI	Power-State Indicator Input. DPRSLPVR and PSI together determine the operating mode and the number of active phases as shown in the truth table included under the PSI pin description above.		
16	TON	Switching Frequency Setting Input. An external resistor between the input power source and TON sets the switching period ($T_{SW} = 1/f_{SW}$) per phase according to the following equation: $T_{SW} = 16.3 \text{pF} \times (R_{TON} + 6.5 \text{k}\Omega)$ TON becomes high impedance in shutdown to reduce the input quiescent current. If the TON current is less than 10µA, the MAX17021/MAX17082/MAX17482 disable the controller, set the TON open fault latch, and pull DL_ and DH_ low.		
17	V3P3	3.3V CLKEN Input Supply. V3P3 input supplies the CLKEN CMOS push-pull logic output. Connect to		
18	CLKEN	Clock Enable Push-Pull Logic Output. This inverted logic output indicates when the output voltage sensed at FB is in regulation. During soft-start, shutdown, and when the FB is out of regulation, the MAX17021/MAX17082/MAX17482 pull CLKEN up to V3P3. During VID transitions, the controller forces CLKEN low. Except during the power-up sequence, CLKEN is the inverse of PWRGD. See the <i>Startup Timing Diagram</i> (Figure 10). When in pulse-skipping mode (DPRSLPVR high), the upper CLKEN threshold is disabled.		
19	PWRGD	Open-Drain Power-Good Output. After output-voltage transitions, except during power-up and power- down; if FB is in regulation then PWRGD is high impedance. During startup, PWRGD is held low and continues to be low while the part is in boot mode and until 5ms (typ) after CLKEN goes low. PWRGD is forced low in shutdown. PWRGD is forced high impedance whenever the slew-rate controller is active (output-voltage transitions). When in pulse-skipping mode (DPRSLPVR high), the upper PWRGD threshold comparator is blanked during downward transitions. A pullup resistor on PWRGD causes additional finite shutdown current.		

M/IXI/N

Pin Description (continued)

PIN	NAME	FUNCTION			
20	PHASEGD	Phase-Good Current-Balance Open-Drain Output. Used to signal the system that one of the two phases either has a fault condition or is not matched with the other. Detection is done by identifying the need for a large on-time difference between phases in order to achieve or move towards current balance. PHASEGD is low in shutdown. PHASEGD is forced high impedance whenever the slew-rate controller is active (output-voltage transitions). PHASEGD is forced high impedance while in one-phase operation (DPRSLPVR = high or PSI = low).			
21	BST2	Boost Flying-Capacitor Connection for Phase 2. BST2 provides the upper supply rail for the DH2 high- side gate driver. An internal switch between V_{DD} and BST2 charges the flying capacitor while the low- side MOSFET is on (DL2 pulled high and LX2 pulled to ground).			
22	LX2	Inductor Connection for Phase 2. LX2 is the internal lower supply rail for the DH2 high-side gate driver. Also used as an input to the controller's zero-crossing comparator for phase 2.			
23	DH2	High-Side Gate-Driver Output for Phase 2. DH2 swings from LX2 to BST2. The controller pulls DH2 low in shutdown.			
24	DL2	Low-Side Gate-Driver Output for Phase 2. DL2 swings from GND to V_{DD} . DL2 is forced low in skip mode after detecting an inductor current zero crossing. DL2 is forced low during one-phase operation (\overline{PSI} = GND or CSP2 = V_{CC}).			
25	VRHOT	Open-Drain Output of Internal Comparator. VRHOT is pulled low when the voltage at THRM goes below 1.5V (30% of V _{CC}). VRHOT is high impedance in shutdown.			
26	V _{DD}	Driver Supply Voltage Input. V _{DD} is the supply voltage used to internally power the low-side gate drivers and refresh the BST_ flying capacitors during the off-times. Connect V _{DD} to the 4.5V to 5.5V system supply voltage. Bypass V _{DD} to the system power ground with a 1 μ F each or greater ceramic capacitor.			
27	DL1	Low-Side Gate-Driver Output for Phase 1. DL1 swings from GND to V _{DD} . DL1 is forced high when an output overvoltage fault is detected, overriding any negative current-limit condition that might be present. DL1 is forced low after soft-shutdown or in skip mode after detecting an inductor current zero crossing.			
28	DH1	High-Side Gate-Driver Output for Phase 1. DH1 swings from LX1 to BST1. The controller pulls DH1 low in shutdown.			
29	LX1	Inductor Connection for Phase 1. LX1 is the internal lower supply rail for the DH1 high-side gate driver. Also used as an input to the controller's zero-crossing comparator for phase 1.			
30	BST1	Boost Flying-Capacitor Connection for Phase 1. BST1 provides the upper supply rail for the DH1 high- side gate driver. An internal switch between V _{DD} and BST1 charges the flying capacitor while the low- side MOSFET is on (DL1 is pulled high and LX1 is pulled to ground).			
31	DPRSTP (MAX17021) SLOW (MAX17082/ MAX17482)	IMVP-6+ Slew-Rate Select Input. This 1.0V logic input signal from the IMVP-6+ system is usually the logical complement of the DPRSLPVR signal. However, the IMVP-6+ specification supports a special slow C4 exit condition that allows both DPRSTP and DPRSLPVR to be pulled high simultaneously. When this occurs, the voltage-transition slew rate reduces to 1/4 the nominal (R _{TIME} -based) slew rate for the duration of this logic condition. The slew rate returns to normal when either DPRSLPVR or DPRSLPVR or DPRSLPVR DPRSTP is pulled low: DPRSLPVR DPRSTP SLEW RATE 0 0 1 Nominal slew rate 1 0 1 0 1 1 Slew rate reduced to 1/4 of nominal IMVP-6.5 Slew-Rate Select Input. This 1.0V logic input signal selects between the nominal and "slow" (half of nominal rate) slew rates. When SLOW is forced high, the selected nominal slew rate is set by the TIME resistance as defined above. When SLOW is forced low, the slew rate is reduced to half the nominal slew rate.			

Pin Description (continued)

PIN	NAME	FUNCTION
		Low-Voltage VID DAC Code Input. The D0-D6 inputs do not have internal pullups. These 1.0V logic
32–38	D0-D6	inputs are designed to interface directly with the CPU. The output voltage is set by the VID code
		indicated by the logic-level voltages on D0–D6 (see Table 4).
		Positive Current-Sense Input for Phase 1. Connect CSP1 to the positive terminal of the inductor current-
39 CSP1	CSP1	sensing resistor or directly to the positive terminal of the filtering capacitor used when the lossless
		DCR sensing method is used (see Figure 4).
		Negative Current-Sense Input for Phase 1. Connect CSN1 to the negative terminal of the inductor
40 CSN1		current-sensing resistor or directly to the negative terminal of the inductor if the lossless DCR sensing
	method is used (see Figure 4).	
		Under V _{CC} UVLO conditions and after soft-shutdown is completed, CSN1 is internally pulled to GND
		through a 10 Ω FET to discharge the output.
		Exposed Pad. Internally connected to GND. Connect to the ground plane through a thermally
— EF	EP	enhanced via. For the MAX17021/MAX17082/MAX17482, the exposed pad is the only GND
		connection and must be properly soldered.



Figure 1. Standard 2-Phase IMVP-6+ Application Circuit

MAX17021/MAX17082/MAX17482

MAX17021/MAX17082/MAX17482

Detailed Description

Table 1 lists the component selection for standard applications. Table 2 lists component suppliers for the MAX17021/MAX17082/MAX17482/MAX17482.

Free-Running, Constant-On-Time PWM Controller with Input Feed-Forward

The Quick-PWM control architecture is a pseudo-fixedfrequency, constant-on-time, current-mode regulator with voltage feed-forward (Figure 3). This architecture relies on the output filter capacitor's ESR to act as the current-sense resistor, so the output ripple voltage provides the PWM ramp signal. The control algorithm is simple: the high-side switch on-time is determined solely by a one-shot whose period is inversely proportional to input voltage, and directly proportional to output voltage or the difference between the main and secondary inductor currents (see the *On-Time One-Shot* section). Another one-shot sets a minimum off-time. The on-time one-shot triggers when the error comparator goes low, the inductor current of the selected phase is below the valley current-limit threshold, and the minimum off-time one-shot times out. The controller maintains 180° out-ofphase operation by alternately triggering the main and secondary phases after the error comparator drops below the output-voltage set point.

Table 1. Component Selection for Standard Applications

DESIGN PARAMETERS	IMVP-6+ SV	IMVP-6+ LV	IMVP-6.5 AUBURNDALE SV CORE	IMVP-6.5 AUBURNDALE LV CORE
CIRCUIT	FIGURE 1	FIGURE 1	FIGURE 2	FIGURE 2
Input-Voltage Range	7V to 20V	7V to 20V	7V to 20V	7V to 20V
Maximum Load Current (TDC Current)	44A (34A)	23A (19A)	50A (37A)	28A (19A)
Transient Load Current	35A (10A/µs)	18A (10A/µs)	35A (10A/µs)	23A (10A/µs)
Load Line	-2.1mV/A	-4mV/A	-1.9mV/A	-3mV/A
COMPONENTS				
TON Resistance (R _{TON})	200 k Ω (f _{SW} = 300 kHz)	200 k Ω (f _{SW} = 300 kHz)	200 k Ω (f _{SW} = 300 kHz)	200 k Ω (f _{SW} = 300 kHz)
Inductance (L)	NEC/TOKIN MPC1055LR36 0.36μH, 32A, 0.8mΩ	NEC/TOKIN MPC1055LR36 0.36μH, 32A, 0.8mΩ	NEC/TOKIN MPC1055LR36 0.36μH, 32A, 0.8mΩ	NEC/TOKIN MPC1055LR36 0.36μH, 32A, 0.8mΩ
High-Side MOSFET (N _H)	Siliconix 1x Si4386DY 7.8m /9.5mΩ (typ/max)			
Low-Side MOSFET (NL)	Siliconix 2x Si4642DY 3.9m /4.7mΩ (typ/max)			
Output Capacitors (COUT)	4x 330μF, 6mΩ, 2.5V Panasonic EEFSX0D0D331XR 28x 10μF, 6V ceramic (0805)	3x 330μF, 6mΩ, 2.5V Panasonic EEFSX0D0D331XR 28x 10μF, 6V ceramic (0805)	4x 330μF, 6mΩ, 2.5V Panasonic EEFSX0D0D331XR 28x 10μF, 6V ceramic (0805)	3x 330μF, 6mΩ, 2.5V Panasonic EEFSX0D0D331XR 28x 10μF, 6V ceramic (0805)
Input Capacitors (CIN)	4x 10μF, 25V ceramic (1210)			

Table 1. Component Selection for Standard Applications (continued)

DESIGN PARAMETERS	IMVP-6+ SV	IMVP-6+ LV	IMVP-6.5 AUBURNDALE SV CORE	IMVP-6.5 AUBURNDALE LV CORE
TIME-ILIM Resistance (R1)	10k Ω	10k Ω	10k Ω	10kΩ
ILIM-GND Resistance (R2)	59k Ω	59k Ω	59k Ω	59kΩ
FB Resistance (R _{FB})	4.32kΩ	8.45kΩ	4.02kΩ	6.34kΩ
IMON Resistance	N/A	N/A	9.09kΩ	18.2kΩ
LXCSP_ Resistance	1.21kΩ	1.21kΩ	1.21kΩ	1.21kΩ
CSPCSN_ Series Resistance (R6)	1.50k Ω	1.50k Ω	1.50k Ω	1.50k Ω
Parallel NTC Resistance	20k Ω	20k Ω	20k Ω	20kΩ
DCR Sense NTC (NTC1)	$10k\Omega$ NTC B = 3380 TDK NTCG163JH103F			
DCR Sense Capacitance (C _{SENSE})	2x 0.22µF, 6V ceramic (0805)			

Table 2. Component Suppliers

SUPPLIER	WEBSITE
AVX Corp.	www.avxcorp.com
BI Technologies	www.bitechnologies.com
Central Semiconductor Corp.	www.centralsemi.com
Fairchild Semiconductor	www.fairchildsemi.com
International Rectifier	www.irf.com
KEMET Corp	www.kemet.com
NEC/TOKIN Corp.	www.nec-tokin.com
Panasonic Corp.	www.panasonic.com

SUPPLIER	WEBSITE
Pulse Engineering	www.pulseeng.com
Renesas Technology Corp.	www.renesas.com
SANYO Electric Co, Ltd.	www.sanyodevice.com
Siliconix (Vishay)	www.vishay.com
Sumida	www.sumida.com
Taiyo Yuden	www.t-yuden.com
TDK Corp.	www.component.tdk.com
TOKO America, Inc.	www.tokoam.com



Figure 2. Standard 2-Phase IMVP-6.5 (Calpella) Application Circuit





Figure 3. Functional Diagram



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MAX17021/MAX17082/MAX17482

Dual 180° Out-of-Phase Operation

The two phases in the MAX17021/MAX17082/ MAX17482 operate 180° out-of-phase to minimize input and output filtering requirements, reduce electromagnetic interference (EMI), and improve efficiency. This effectively lowers component count—reducing cost, board space, and component power requirements—making the MAX17021/MAX17082/MAX17482 ideal for high-power, cost-sensitive applications.

Typically, switching regulators provide power using only one phase instead of dividing the power among several phases. In these applications, the input capacitors must support high instantaneous current requirements. The high RMS ripple current can lower efficiency due to I²R power loss associated with the input capacitor's effective series resistance (ESR). Therefore, the system typically requires several low-ESR input capacitors in parallel to minimize input-voltage ripple, to reduce ESR-related power losses, and to meet the necessary RMS ripple current rating.

With the MAX17021/MAX17082/MAX17482, the controller shares the current between two phases that operate 180° out-of-phase, so the high-side MOSFETs never turn on simultaneously during normal operation. The instantaneous input current of either phase is effectively halved, resulting in reduced input-voltage ripple, ESR power loss, and RMS ripple current (see the *Input Capacitor Selection* section). Therefore, the same performance can be achieved with fewer or less-expensive input capacitors.

+5V Bias Supply (Vcc and VDD)

The Quick-PWM controller requires an external +5V bias supply in addition to the battery. Typically, this +5V bias supply is the notebook's 95% efficient +5V system supply. Keeping the bias supply external to the IC improves efficiency and eliminates the cost associated with the +5V linear regulator that would otherwise be needed to supply the PWM circuit and gate drivers. If stand-alone capability is needed, the +5V bias supply can be generated with an external linear regulator.

The +5V bias supply must provide V_{CC} (PWM controller) and V_{DD} (gate-drive power), so the maximum current drawn is:

IBIAS = ICC + fSW (QG(LOW) + QG(HIGH))

where I_{CC} is provided in the *Electrical Characteristics* table, f_{SW} is the switching frequency, and Q_{G(LOW)} and Q_{G(HIGH)} are the MOSFET data sheet's total gate-charge specification limits at V_{GS} = 5V.

 V_{IN} and V_{DD} can be tied together if the input power source is a fixed +4.5V to +5.5V supply. If the +5V bias supply is powered-up prior to the battery supply, the enable signal (SHDN going from low to high) must be delayed until the battery voltage is present to ensure startup.

Switching Frequency (TON)

Connect a resistor (R_{TON}) between TON and V_{IN} to set the switching period $T_{SW} = 1/f_{SW}$, per phase:

$$\Gamma_{SW} = 16.3 \text{pF} \times (\text{R}_{TON} + 6.5 \text{k}\Omega)$$

A 96.75k Ω to 303.25k Ω corresponds to switching periods of 167ns (600kHz) to 500ns (200kHz), respectively. High-frequency (600kHz) operation optimizes the application for the smallest component size, trading off efficiency due to higher switching losses. This might be acceptable in ultra-portable devices where the load currents are lower and the controller is powered from a lower voltage supply. Low-frequency (200kHz) operation offers the best overall efficiency at the expense of component size and board space.

TON Open-Circuit Protection

The TON input includes open-circuit protection to avoid long, uncontrolled on-times that could result in an over-voltage condition on the output. The MAX17021/MAX17082/MAX17482 detect an open-circuit fault if the TON current drops below 10 μ A for any reason—the TON resistor (R_{TON}) is unpopulated, a high resistance value is used, the input voltage is low, etc. Under these conditions, the MAX17021/MAX17082/MAX17482 stop switching (DH_ and DL_ pulled low) and immediately set the fault latch. Toggle SHDN or cycle the V_{CC} power supply below 0.5V to clear the fault latch and reactivate the controller.

On-Time One-Shot

The core of each phase contains a fast, low-jitter, adjustable one-shot that sets the high-side MOSFETs on-time. The one-shot for the main phase varies the on-time in response to the input and feedback voltages. The main high-side switch on-time is inversely proportional to the input voltage as measured by the TON input, and proportional to the feedback voltage (VFB):

$$t_{ON(MAIN)} = \frac{T_{SW} \left(V_{FB} + 0.075 V \right)}{V_{IN}}$$

where the switching period ($T_{SW} = 1/f_{SW}$) is set by the resistor at the TON pin, and 0.075V is an approximation to accommodate the expected drop across the low-side MOSFET switch.

The one-shot for the secondary phase varies the ontime in response to the input voltage and the difference between the main and secondary inductor currents. Two identical transconductance amplifiers integrate the



difference between the master and slave current-sense signals. The summed output is internally connected to CCI, allowing adjustment of the integration time constant with a compensation network connected between CCI and FB. The resulting compensation current and voltage are determined by the following equations:

$$\label{eq:ccl} \begin{split} \mathsf{ICCI} &= \mathsf{G}_{\mathsf{m}}(\mathsf{VCSP1} - \mathsf{VCSN1}) - \mathsf{G}_{\mathsf{m}}(\mathsf{VCSP2} - \mathsf{VCSN2}) \\ \\ \mathsf{VCCI} &= \mathsf{VFB} + \mathsf{ICCIZCCI} \end{split}$$

where Z_{CCI} is the impedance at the CCI output. The secondary on-time one-shot uses this integrated signal (V_{CCI}) to set the secondary high-side MOSFETs ontime. When the main and secondary current-sense signals (V_{CM} = V_{CSP1} - V_{CSN1} and V_{CS} = V_{CSP2} - V_{CSN2}) become unbalanced, the transconductance amplifiers adjust the secondary on-time, which increases or decreases the secondary inductor current until the current-sense signals are properly balanced:

$$\begin{split} t_{ON(SEC)} &= T_{SW} \left(\frac{V_{CCI} + 0.075V}{V_{IN}} \right) \\ &= T_{SW} \left(\frac{V_{FB} + 0.075V}{V_{IN}} \right) + T_{SW} \left(\frac{I_{CCI}Z_{CCI}}{V_{IN}} \right) \\ &= (Main \ On-time) + (Secondary \ Current \ Balance \ Correction) \end{split}$$

This algorithm results in a nearly constant switching frequency and balanced inductor currents despite the lack of a fixed-frequency clock generator. The benefits of a constant switching frequency are twofold: first, the frequency can be selected to avoid noise-sensitive regions such as the 455kHz IF band; second, the inductor ripple-current operating point remains relatively constant, resulting in easy design methodology and predictable output-voltage ripple. The on-time oneshots have good accuracy at the operating points specified in the *Electrical Characteristics* table. Ontimes at operating points far removed from the conditions specified in the *Electrical Characteristics* table can vary over a wider range.

On-times translate only roughly to switching frequencies. The on-times guaranteed in the *Electrical Characteristics* table are influenced by switching delays in the external high-side MOSFET. Resistive losses, including the inductor, both MOSFETs, output capacitor ESR, and PCB copper losses in the output and ground tend to raise the switching frequency at higher output currents. Also, the dead-time effect increases the effective on-time, reducing the switching frequency. It occurs only during forced-PWM operation and dynamic output-voltage transitions when the inductor current reverses at light- or negative-load currents. With reversed inductor current, the inductor's EMF causes LX_ to go high earlier than normal, extending the on-time by a period equal to the DH_-rising dead time. For loads above the critical conduction point, where the dead-time effect is no longer a factor, the actual switching frequency (per phase) is:

$$f_{SW} = \frac{\left(V_{OUT} + V_{DIS}\right)}{t_{ON}\left(V_{IN} + V_{DIS} - V_{CHG}\right)}$$

where V_{DIS} is the sum of the parasitic voltage drops in the inductor discharge path, including synchronous rectifier, inductor, and PCB resistances; V_{CHG} is the sum of the parasitic voltage drops in the inductor charge path, including high-side switch, inductor, and PCB resistances; and to_N is the on-time as determined above.

Current Sense

The output current of each phase is sensed. Low-offset amplifiers are used for current balance, voltage-positioning gain, and current limit. Sensing the current at the output of each phase offers advantages, including less noise sensitivity, more accurate current sharing between phases, and the flexibility of using either a current-sense resistor or the DC resistance of the output inductor.

Using the DC resistance (R_{DCR}) of the output inductor allows higher efficiency. In this configuration, the initial tolerance and temperature coefficient of the inductor's DCR must be accounted for in the output-voltage droop-error budget and power monitor. This currentsense method uses an RC filtering network to extract the current information from the output inductor (see Figure 4). The resistive divider used should provide a current-sense resistance (R_{CS}) low enough to meet the current-limit requirements, and the time constant of the RC network should match the inductor's time constant (L/R_{CS}):

$$R_{CS} = \left(\frac{R2}{R1 + R2}\right) R_{DCR}$$

and:

$$\mathsf{R}_{\text{CS}} = \frac{\mathsf{L}}{\mathsf{C}_{\text{EQ}}} \left[\frac{1}{\mathsf{R1}} + \frac{1}{\mathsf{R2}} \right]$$

where R_{CS} is the required current-sense resistance and R_{DCR} is the inductor's series DC resistance.